

Application No. 10/822,642

AMENDMENTS TO THE SPECIFICATIONIn the Specification

At page 31, lines 16-22, please replace the paragraph with the following.

The deposition of coatings of dielectric materials for chip capacitors is described in copending and commonly assigned U.S. Patent Application serial number 10/219,019, now U.S. Patent 6,917,511 to Bryan, entitled "Reactive Deposition For The Formation Of Chip Capacitors," incorporated herein by reference. Suitable dielectric materials include a majority of barium titanate (BaTiO_3), optionally mixed with other metal oxides. Other dielectric oxides suitable for incorporation into ceramic chip capacitors with appropriate dopant(s)/additive(s) comprise, for example, SrTiO_3 , CaTiO_3 , SrZrO_3 , CaZrO_3 , $\text{Nd}_2\text{O}_3\text{-}2\text{TiO}_3$, $\text{La}_2\text{O}_3\text{-}2\text{TiO}_2$, and the like, and any two or more thereof.

At page 45, line 28 to page 46, line 17, please replace the paragraph with the following.

Reasonable lengths for reactant inlet 474 for the production of ceramic submicron/nanoscale particles, when used with an 1800 watt CO_2 laser, are in the range(s) from about 5 mm to about 1 meter. More specifically with respect to the reactant inlet, the inlet generally has an elongated dimension in the range(s) of at least about 0.5 inches (1.28 cm), in other embodiments in the range(s) of at least about 1.5 inches (3.85 cm), in other embodiments in the range(s) of at least about 2 inches (5.13 cm), in further embodiments in the range(s) of at least about 3 inches (7.69 cm), in further embodiments in the range(s) of at least about 5 inches (12.82 cm) and in additional embodiments in the range(s) from about 8 inches (20.51 cm) to about 200 inches (5.13 meters). A person of ordinary skill in the art will recognize that additional ranges of inlet lengths within these

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specific ranges are contemplated and are within the present disclosure. In addition, the inlet can be characterized by an aspect ratio that is the ratio of the length divided by the width. If the inlet is not rectangular, the aspect ratio can be evaluated using the longest dimension as the length and the width as the largest dimension perpendicular to the line segment along the length. In some embodiments, the aspect ratio is in the range(s) of at least about 5, in other embodiments in the range(s) of at least about 10 and in further embodiments, in the range(s) from about 50 to about 400. A person of ordinary skill in the art will recognize that additional ranges of aspect ratio within these explicit ranges of aspect ratio are contemplated and are within the present disclosure. Nozzle parameters for particle production by laser pyrolysis are described further in copending U.S. Patent application serial number 10/119,645, now U.S. Patent 6,919,054 to Gardner et al., entitled "Reactant Nozzles Within Flowing Reactors," incorporated herein by reference.

At page 54, line 20 to page 55, line 2, please replace the paragraph with the following.

The formation of coatings by light reactive deposition, silicon glass deposition and optical devices in general are described further in copending and commonly assigned U.S. Patent Application 09/715,935 to Bi et al., entitled "Coating Formation By Reactive Deposition," incorporated herein by reference, and in copending and commonly assigned PCT application designating the U.S. serial number PCT/US01/32413 to Bi et al. filed on October 16, 2001, entitled "Coating Formation By Reactive Deposition," incorporated herein by reference. Also, using light reactive deposition, a range of effective approaches are available to vary the chemical composition of optical materials within layers and in different layers to form three-dimensional optical structures with selected compositions at selected positions within the material. The patterning of compositions of optical materials during the deposition process is described further in copending and commonly

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assigned U.S. Patent application 10/027,906, now U.S. Patent 6,952,504 to Bi et al., entitled "Three Dimensional Engineering of Optical Structures," incorporated herein by reference.